F m PTO-1449 (Rev. 8-83) JAN 0 4 1999 Department of Commerce

Att rney D ck t N . 0756-1638

Serial N . 08/807,737

INFORMATION DISCLOSURE STATEMENT

(Use several she ts if necessary)

Applicant: Hisashi OHTANI et al.

Filing Date: February 27, 1997

Group: 2813

U.S.	PAT	ENT	DOC	JMENTS
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\*EXAMINER: Initial if citation considered, which is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Includicopy of this form with next communication to applicant.

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	U.S. Department of Commerce Patent and Trademark Office		Attorney D ck t N . 0756-1638		Serial N . 08/807,737		
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